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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M7
Core Size	32-Bit Single-Core
Speed	216MHz
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, IrDA, LINbus, SAI, SD, SPDIF-Rx, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	140
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	320K x 8
Voltage - Supply (Vcc/Vdd)	1.7V ~ 3.6V
Data Converters	A/D 24x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f746iet6

2.15 Boot modes

At startup, the boot memory space is selected by the BOOT pin and BOOT_ADDx option bytes, allowing to program any boot memory address from 0x0000 0000 to 0x3FFF FFFF which includes:

- All Flash address space mapped on ITCM or AXIM interface
- All RAM address space: ITCM, DTCM RAMs and SRAMs mapped on AXIM interface
- The System memory bootloader

The boot loader is located in system memory. It is used to reprogram the Flash memory through a serial interface.

2.16 Power supply schemes

- V_{BAT} = 1.65 to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.
- V_{DD} = 1.7 to 3.6 Vexternal power supply for I/Os and the internal regulator (when enabled), provided externally through V_{DD} pins.
- V_{SSA}, V_{DDA} = 1.7 to 3.6 V: external analog power supplies for ADC, DAC, reset blocks, RCs and PLL. V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS}, respectively.

Note: V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the internal reset is OFF (refer to Section 2.17.2: Internal reset OFF). Refer to Table 3: Voltage regulator configuration mode versus device operating mode to identify the packages supporting this option.

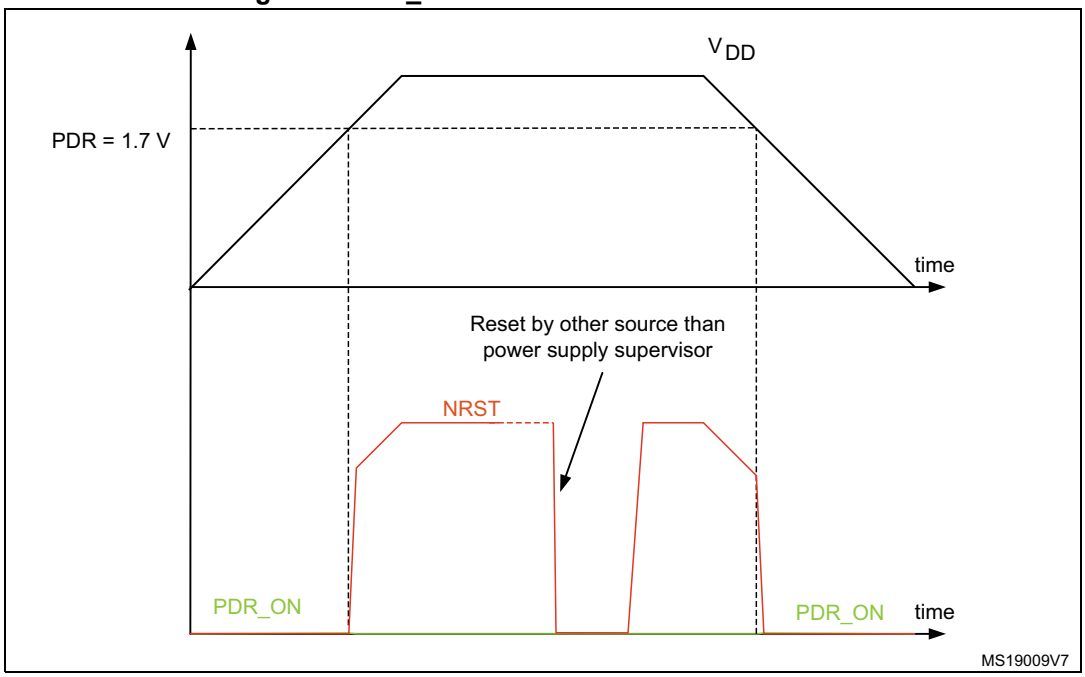
- V_{DDUSB} can be connected either to V_{DD} or an external independent power supply (3.0 to 3.6V) for USB transceivers (refer to *Figure 4* and *Figure 5*). For example, when device is powered at 1.8V, an independent power supply 3.3V can be connected to V_{DDUSB}. When the V_{DDUSB} is connected to a separated power supply, it is independent from V_{DD} or V_{DDA} but it must be the last supply to be provided and the first to disappear. The following conditions V_{DDUSB} must be respected:
  - During power-on phase ($V_{DD} < V_{DD\_MIN}$), V_{DDUSB} should be always lower than V_{DD}
  - During power-down phase ($V_{DD} < V_{DD\_MIN}$), V_{DDUSB} should be always lower than V_{DD}
  - V_{DDSUB} rising and falling time rate specifications must be respected (see *Table 20* and *Table 21*)
  - In operating mode phase, V_{DDUSB} could be lower or higher than V_{DD}:

    - If USB (USB OTG_HS/OTG_FS) is used, the associated GPIOs powered by V_{DDUSB} are operating between V_{DDUSB_MIN} and V_{DDUSB_MAX}.

    - The V_{DDUSB} supply both USB transceiver (USB OTG_HS and USB OTG_FS). If only one USB transceiver is used in the application, the GPIOs associated to the other USB transceiver are still supplied by V_{DDUSB}.

    - If USB (USB OTG_HS/OTG_FS) is not used, the associated GPIOs powered by V_{DDUSB} are operating between V_{DD_MIN} and V_{DD_MAX}.

Figure 7. PDR_ON control with internal reset OFF



2.18 Voltage regulator

The regulator has four operating modes:

- Regulator ON
  - Main regulator mode (MR)
  - Low-power regulator (LPR)
  - Power-down
- Regulator OFF

2.18.1 Regulator ON

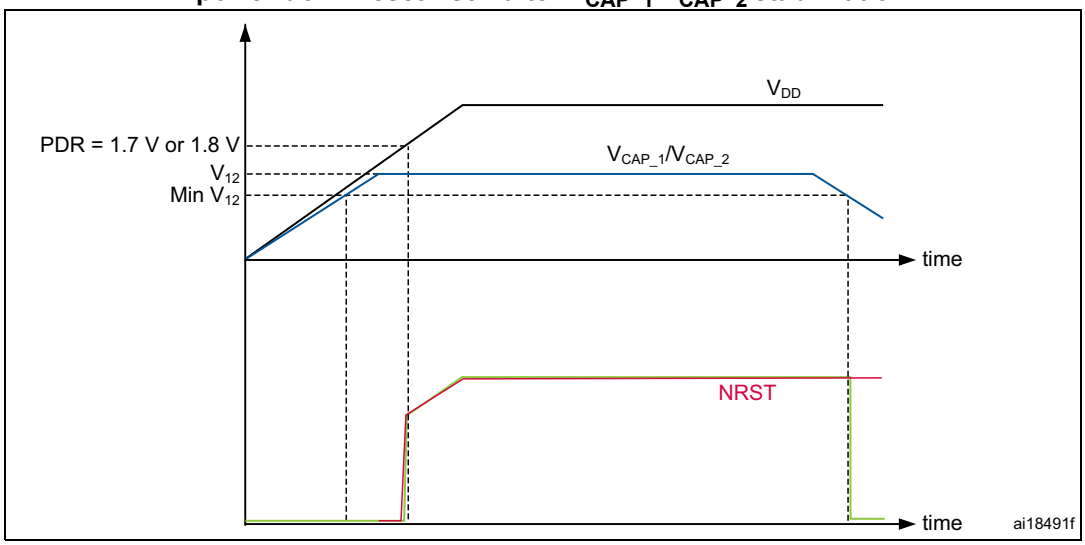
On packages embedding the BYPASS_REG pin, the regulator is enabled by holding BYPASS_REG low. On all other packages, the regulator is always enabled.

There are three power modes configured by software when the regulator is ON:

- MR mode used in Run/sleep modes or in Stop modes
  - In Run/Sleep mode

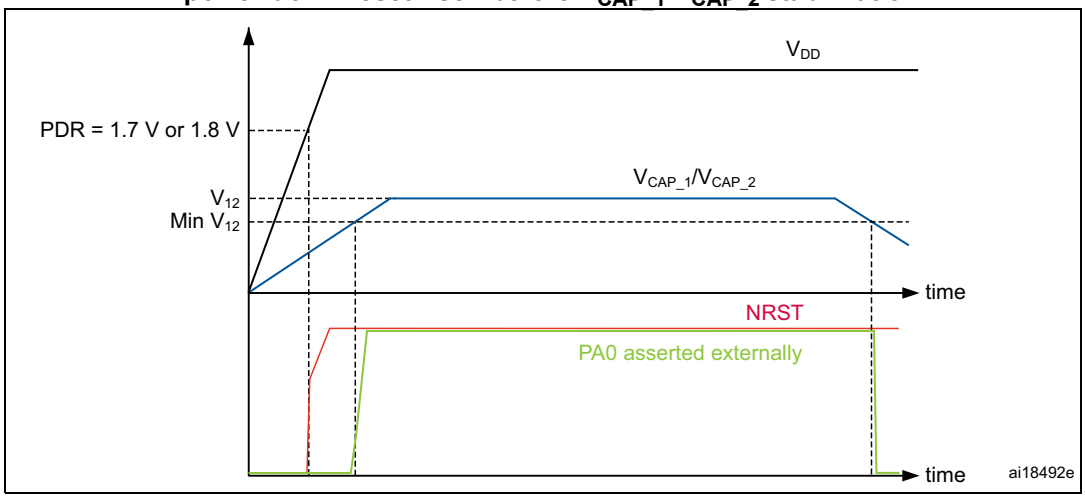
    The MR mode is used either in the normal mode (default mode) or the over-drive mode (enabled by software). Different voltages scaling are provided to reach the best compromise between the maximum frequency and dynamic power

Figure 9. Startup in regulator OFF: slow V_{DD} slope - power-down reset risen after V_{CAP_1}/V_{CAP_2} stabilization



1. This figure is valid whatever the internal reset mode (ON or OFF).

Figure 10. Startup in regulator OFF mode: fast V_{DD} slope - power-down reset risen before V_{CAP_1}/V_{CAP_2} stabilization



1. This figure is valid whatever the internal reset mode (ON or OFF).

2.21 V_{BAT} operation

The V_{BAT} pin allows to power the device V_{BAT} domain from an external battery, an external supercapacitor, or from V_{DD} when no external battery and an external supercapacitor are present.

V_{BAT} operation is activated when V_{DD} is not present.

The V_{BAT} pin supplies the RTC, the backup registers and the backup SRAM.

Note: When the microcontroller is supplied from V_{BAT}, external interrupts and RTC alarm/events do not exit it from V_{BAT} operation.

When PDR_ON pin is connected to V_{SS} (Internal Reset OFF), the V_{BAT} functionality is no more available and V_{BAT} pin should be connected to V_{DD}.

2.22 Timers and watchdogs

The devices include two advanced-control timers, eight general-purpose timers, two basic timers and two watchdog timers.

All timer counters can be frozen in debug mode.

Table 6 compares the features of the advanced-control, general-purpose and basic timers.

2.22.3 Basic timers TIM6 and TIM7

These timers are mainly used for DAC trigger and waveform generation. They can also be used as a generic 16-bit time base.

TIM6 and TIM7 support independent DMA request generation.

2.22.4 Low-power timer (LPTIM1)

The low-power timer has an independent clock and is running also in Stop mode if it is clocked by LSE, LSI or an external clock. It is able to wakeup the devices from Stop mode.

This low-power timer supports the following features:

- 16-bit up counter with 16-bit autoreload register
- 16-bit compare register
- Configurable output: pulse, PWM
- Continuous / one-shot mode
- Selectable software / hardware input trigger
- Selectable clock source:
- Internal clock source: LSE, LSI, HSI or APB clock
- External clock source over LPTIM input (working even with no internal clock source running, used by the Pulse Counter Application)
- Programmable digital glitch filter
- Encoder mode

2.22.5 Independent watchdog

The independent watchdog is based on a 12-bit downcounter and 8-bit prescaler. It is clocked from an independent 32 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free-running timer for application timeout management. It is hardware- or software-configurable through the option bytes.

2.22.6 Window watchdog

The window watchdog is based on a 7-bit downcounter that can be set as free-running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the main clock. It has an early warning interrupt capability and the counter can be frozen in debug mode.

2.22.7 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard downcounter. It features:

- A 24-bit downcounter
- Autoreload capability
- Maskable system interrupt generation when the counter reaches 0
- Programmable clock source.

2.24 Universal synchronous/asynchronous receiver transmitters (USART)

The device embeds USART. Refer to *Table 8: USART implementation* for the features implementation.

The universal synchronous asynchronous receiver transmitter (USART) offers a flexible means of full-duplex data exchange with external equipment requiring an industry standard NRZ asynchronous serial data format.

The USART peripheral supports:

- Full-duplex asynchronous communications
- Configurable oversampling method by 16 or 8 to give flexibility between speed and clock tolerance
- Dual clock domain allowing convenient baud rate programming independent from the PCLK reprogramming
- A common programmable transmit and receive baud rate of up to 27 Mbit/s when USART clock source is system clock frequency (Max is 216 MHz) and oversampling by 8 is used.
- Auto baud rate detection
- Programmable data word length (7 or 8 or 9 bits) word length
- Programmable data order with MSB-first or LSB-first shifting
- Programmable parity (odd, even, no parity)
- Configurable stop bits (1 or 1.5 or 2 stop bits)
- Synchronous mode and clock output for synchronous communications
- Single-wire half-duplex communications
- Separate signal polarity control for transmission and reception
- Swappable Tx/Rx pin configuration
- Hardware flow control for modem and RS-485 transceiver
- Multiprocessor communications
- LIN master synchronous break send capability and LIN slave break detection capability
- IrDA SIR encoder decoder supporting 3/16 bit duration for normal mode
- Smartcard mode (T=0 and T=1 asynchronous protocols for Smartcards as defined in the ISO/IEC 7816-3 standard)
- Support for Modbus communication

The table below summarizes the implementation of all U(S)ARTs instances

Table 8. USART implementation

features(1)	USART1/2/3/6	UART4/5/7/8
Data Length	7, 8 and 9 bits	
Hardware flow control for modem	X	X
Continuous communication using DMA	X	X
Multiprocessor communication	X	X
Synchronous mode	X	-

2.38 General-purpose input/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain, with or without pull-up or pull-down), as input (floating, with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high-current-capable and have speed selection to better manage internal noise, power consumption and electromagnetic emission.

The I/O configuration can be locked if needed by following a specific sequence in order to avoid spurious writing to the I/Os registers.

Fast I/O handling allowing maximum I/O toggling up to 108 MHz.

2.39 Analog-to-digital converters (ADCs)

Three 12-bit analog-to-digital converters are embedded and each ADC shares up to 16 external channels, performing conversions in the single-shot or scan mode. In scan mode, automatic conversion is performed on a selected group of analog inputs.

Additional logic functions embedded in the ADC interface allow:

- Simultaneous sample and hold
- Interleaved sample and hold

The ADC can be served by the DMA controller. An analog watchdog feature allows very precise monitoring of the converted voltage of one, some or all selected channels. An interrupt is generated when the converted voltage is outside the programmed thresholds.

To synchronize A/D conversion and timers, the ADCs could be triggered by any of TIM1, TIM2, TIM3, TIM4, TIM5, or TIM8 timer.

2.40 Temperature sensor

The temperature sensor has to generate a voltage that varies linearly with temperature. The conversion range is between 1.7 V and 3.6 V. The temperature sensor is internally connected to the same input channel as V_{BAT}, ADC1_IN18, which is used to convert the sensor output voltage into a digital value. When the temperature sensor and V_{BAT} conversion are enabled at the same time, only V_{BAT} conversion is performed.

As the offset of the temperature sensor varies from chip to chip due to process variation, the internal temperature sensor is mainly suitable for applications that detect temperature changes instead of absolute temperatures. If an accurate temperature reading is needed, then an external temperature sensor part should be used.

2.41 Digital-to-analog converter (DAC)

The two 12-bit buffered DAC channels can be used to convert two digital signals into two analog voltage signal outputs.

Table 10. STM32F745xx and STM32F746xx pin and ball definition (continued)

Pin Number								Pin name (function after reset)(1)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
LQFP100	TFBGA100	WLCSP143	LQFP144	UFBGA176	LQFP176	LQFP208	TFBGA216						
41	H6	K4	64	P10	74	85	P10	PE11	I/O	FT	-	TIM1_CH2, SPI4_NSS, SAI2_SD_B, FMC_D8, LCD_G3, EVENTOUT	-
42	J6	L4	65	R10	75	86	R10	PE12	I/O	FT	-	TIM1_CH3N, SPI4_SCK, SAI2_SCK_B, FMC_D9, LCD_B4, EVENTOUT	-
43	K6	N4	66	N11	76	87	R12	PE13	I/O	FT	-	TIM1_CH3, SPI4_MISO, SAI2_FS_B, FMC_D10, LCD_DE, EVENTOUT	-
44	G7	M4	67	P11	77	88	P11	PE14	I/O	FT	-	TIM1_CH4, SPI4_MOSI, SAI2_MCK_B, FMC_D11, LCD_CLK, EVENTOUT	-
45	H7	L3	68	R11	78	89	R11	PE15	I/O	FT	-	TIM1_BKIN, FMC_D12, LCD_R7, EVENTOUT	-
46	J7	M3	69	R12	79	90	P12	PB10	I/O	FT	-	TIM2_CH3, I2C2_SCL, SPI2_SCK/I2S2_CK, USART3_TX, OTG_HS_ULPI_D3, ETH_MII_RX_ER, LCD_G4, EVENTOUT	-
47	K7	N3	70	R13	80	91	R13	PB11	I/O	FT	-	TIM2_CH4, I2C2_SDA, USART3_RX, OTG_HS_ULPI_D4, ETH_MII_TX_EN/ETH_RMII_TX_EN, LCD_G5, EVENTOUT	-
48	F8	N2	71	M10	81	92	L11	VCAP_1	S	-	-	-	-
49	-	H2	-	-	-	93	K9	VSS	S	-	-	-	-
50	-	J6	72	N10	82	94	L10	VDD	S	-	-	-	-
-	-	-	-	-	-	95	M14	PJ5	I/O	FT	-	LCD_R6, EVENTOUT	-
-	-	-	-	M11	83	96	P13	PH6	I/O	FT	-	I2C2_SMBA, SPI5_SCK, TIM12_CH1, ETH_MII_RXD2, FMC_SDNE1, DCMI_D8, EVENTOUT	-

Table 12. STM32F745xx and STM32F746xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11/LPTIM1/CEC	I2C1/2/3/4/CEC	SPI1/2/3/4/5/6	SPI3/SAI1	SPI2/3/USART1/2/3/UART5/SPDIFRX	SAI2/USART6/UART4/5/7/8/SPDIFRX	CAN1/2/TIM12/13/14/QUADSPI/LCD	SAI2/QUADSPI/OTG2_HS/OTG1_FS	ETH/OTG1_FS	FMC/SDMMC1/OTG2_FS	DCMI	LCD	SYS
Port C	PC4	-	-	-	-	-	I2S1_MCK	-	-	SPDIFRX_IN2	-	-	ETH_MII_RXD0/ETH_RMII_RXD0	FMC_SDNE0	-	-	EVENTOUT
	PC5	-	-	-	-	-	-	-	-	SPDIFRX_IN3	-	-	ETH_MII_RXD1/ETH_RMII_RXD1	FMC_SDCKE0	-	-	EVENTOUT
	PC6	-	-	TIM3_CH1	TIM8_CH1	-	I2S2_MCK	-	-	USART6_TX	-	-	-	SDMMC1_D6	DCMI_D0	LCD_HSYNC	EVENTOUT
	PC7	-	-	TIM3_CH2	TIM8_CH2	-	-	I2S3_MCK	-	USART6_RX	-	-	-	SDMMC1_D7	DCMI_D1	LCD_G6	EVENTOUT
	PC8	TRACED1	-	TIM3_CH3	TIM8_CH3	-	-	-	UART5_RTS	USART6_CK	-	-	-	SDMMC1_D0	DCMI_D2	-	EVENTOUT
	PC9	MCO2	-	TIM3_CH4	TIM8_CH4	I2C3_SDA	I2S_CKIN	-	UART5_CTS	-	QUADSPI_BK1_IO0	-	-	SDMMC1_D1	DCMI_D3	-	EVENTOUT
	PC10	-	-	-	-	-	-	SPI3_SCK/I2S3_CK	USART3_TX	UART4_TX	QUADSPI_BK1_IO1	-	-	SDMMC1_D2	DCMI_D8	LCD_R2	EVENTOUT
	PC11	-	-	-	-	-	-	SPI3_MISO	USART3_RX	UART4_RX	QUADSPI_BK2_NCS	-	-	SDMMC1_D3	DCMI_D4	-	EVENTOUT
	PC12	TRACED3	-	-	-	-	-	SPI3_MOSI/I2S3_SD	USART3_CK	UART5_TX	-	-	-	SDMMC1_CK	DCMI_D9	-	EVENTOUT
	PC13	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PC14	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PC15	-	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT

Table 12. STM32F745xx and STM32F746xx alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11/LPTIM1/CEC	I2C1/2/3/4/CEC	SPI1/2/3/4/5/6	SPI3/SAI1	SPI2/3/USART1/2/3/UART5/SPDIFRX	SAI2/USART6/UART4/5/7/8/SPDIFRX	CAN1/2/TIM12/13/14/QUADSPI/LCD	SAI2/QUADSPI/OTG2_HS/OTG1_FS	ETH/OTG1_FS	FMC/SDMMC1/OTG2_FS	DCMI	LCD	SYS
Port J	PJ7	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_G0	EVENTOUT
	PJ8	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_G1	EVENTOUT
	PJ9	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_G2	EVENTOUT
	PJ10	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_G3	EVENTOUT
	PJ11	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_G4	EVENTOUT
	PJ12	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B0	EVENTOUT
	PJ13	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B1	EVENTOUT
	PJ14	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B2	EVENTOUT
	PJ15	-	-	-	-	-	-	-	-	-	-	-	-	-	-	LCD_B3	EVENTOUT

Table 32. Typical and maximum current consumptions in Standby mode

Symbol	Parameter	Conditions	Typ(1)			Max(2)			Unit
			T_A = 25 °C			T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
			V_{DD} = 1.7 V	V_{DD}= 2.4 V	V_{DD} = 3.3 V	V_{DD} = 3.3 V			
I_{DD_STBY}	Supply current in Standby mode	Backup SRAM OFF, RTC and LSE OFF	1.7	1.9	2.3	5(3)	15(3)	31(3)	µA
		Backup SRAM ON, RTC and LSE OFF	2.4	2.6	3.0	6(3)	20(3)	40(3)	
		Backup SRAM OFF, RTC ON and LSE in low drive mode	2.1	2.4	2.9	6	19	39	
		Backup SRAM OFF, RTC ON and LSE in medium low drive mode	2.1	2.4	2.9	6	19	39	
		Backup SRAM OFF, RTC ON and LSE in medium high drive mode	2.2	2.5	3.0	7	20	40	
		Backup SRAM OFF, RTC ON and LSE in high drive mode	2.3	2.6	3.1	7	20	42	
		Backup SRAM ON, RTC ON and LSE in low drive mode	2.7	3.0	3.6	8	23	49	
		Backup SRAM ON, RTC ON and LSE in Medium low drive mode	2.7	3.0	3.6	8	23	49	
		Backup SRAM ON, RTC ON and LSE in Medium high drive mode	2.8	3.1	3.7	8	24	50	
		Backup SRAM ON, RTC ON and LSE in High drive mode	2.9	3.2	3.8	8	25	51	

1. PDR is OFF for V_{DD}=1.7V. When the PDR is OFF (internal reset OFF), the typical current consumption is reduced by additional 1.2 µA.
2. Guaranteed by characterization results.
3. Based on characterization, tested in production.

Table 40. LSE oscillator characteristics (f_{LSE} = 32.768 kHz) (1) (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
G_m_crit_max	Maximum critical crystal g_m	LSEDRV[1:0]=00 Low drive capability	-	-	0.48	µA/V
		LSEDRV[1:0]=10 Medium low drive capability	-	-	0.75	
		LSEDRV[1:0]=01 Medium high drive capability	-	-	1.7	
		LSEDRV[1:0]=11 High drive capability	-	-	2.7	
t_{SU}(2)	start-up time	V_{DD} is stabilized	-	2	-	s

1. Guaranteed by design.
2. Guaranteed by characterization results. t_{SU} is the start-up time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal manufacturer.

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 33. Typical application with a 32.768 kHz crystal

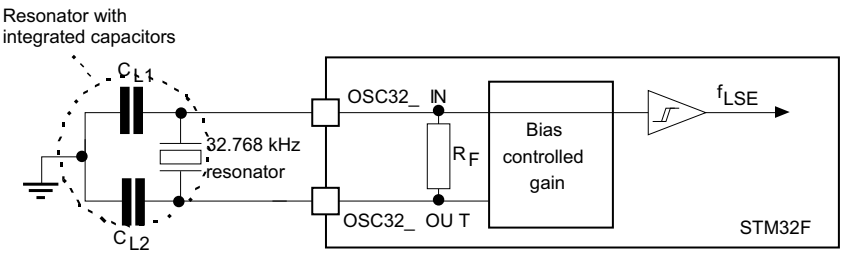


Table 56. I/O static characteristics (continued)

Symbol	Parameter		Conditions	Min	Typ	Max	Unit
V_{IH}	FT, TTa and NRST I/O input high level voltage(5)		1.7 V≤V_{DD}≤3.6 V	$0.45V_{DD}+0.3$(1)	-	-	V
				$0.7V_{DD}$(2)			
	BOOT I/O input high level voltage		1.75 V≤V_{DD} ≤3.6 V, –40 °C≤T_A ≤105 °C	$0.17V_{DD}+0.7$(1)	-	-	
			1.7 V≤V_{DD} ≤3.6 V, 0 °C≤T_A ≤105 °C				
V_{HYS}	FT, TTa and NRST I/O input hysteresis		1.7 V≤V_{DD}≤3.6 V	$10\%V_{DD}$(3)	-	-	V
	BOOT I/O input hysteresis		1.75 V≤V_{DD} ≤3.6 V, –40 °C≤T_A ≤105 °C	0.1	-	-	
			1.7 V≤V_{DD} ≤3.6 V, 0 °C≤T_A ≤105 °C				
I_{lkg}	I/O input leakage current (4)		V_{SS} ≤V_{IN} ≤V_{DD}	-	-	±1	µA
	I/O FT input leakage current (5)		V_{IN} = 5 V	-	-	3	
R_{PU}	Weak pull-up equivalent resistor(6)	All pins except for PA10/PB12 (OTG_FS_ID ,OTG_HS_ID)	V_{IN} = V_{SS}	30	40	50	kΩ
		PA10/PB12 (OTG_FS_ID ,OTG_HS_ID)		7	10	14	
R_{PD}	Weak pull-down equivalent resistor(7)	All pins except for PA10/PB12 (OTG_FS_ID ,OTG_HS_ID)	V_{IN} = V_{DD}	30	40	50	
		PA10/PB12 (OTG_FS_ID ,OTG_HS_ID)		7	10	14	
C_{IO}(8)	I/O pin capacitance		-	-	5	-	pF

1. Guaranteed by design.
2. Tested in production.
3. With a minimum of 200 mV.
4. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins, Refer to *Table 55: I/O current injection susceptibility*
5. To sustain a voltage higher than VDD +0.3 V, the internal pull-up/pull-down resistors must be disabled. Leakage could be higher than the maximum value, if negative current is injected on adjacent pins.Refer to *Table 55: I/O current injection susceptibility*
6. Pull-up resistors are designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is minimum (~10% order).

Table 62. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{VREF+}(2)	ADC V_{REF} DC current consumption in conversion mode	-	-	300	500	µA
I_{VDDA}(2)	ADC V_{DDA} DC current consumption in conversion mode	-	-	1.6	1.8	mA

1. V_{DDA} minimum value of 1.7 V is obtained with the use of an external power supply supervisor (refer to *Section 2.17.2: Internal reset OFF*).
2. Guaranteed by characterization results.
3. V_{REF+} is internally connected to V_{DDA} and V_{REF-} is internally connected to V_{SSA}.
4. R_{ADC} maximum value is given for V_{DD}=1.7 V, and minimum value for V_{DD}=3.3 V.
5. For external triggers, a delay of $1/f_{PCLK2}$ must be added to the latency specified in *Table 62*.

Equation 1: R_{AIN} max formula

$$R_{AIN} = \frac{(k - 0.5)}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. N = 12 (from 12-bit resolution) and k is the number of sampling periods defined in the ADC_SMPR1 register.

Table 63. ADC static accuracy at f_{ADC} = 18 MHz

Symbol	Parameter	Test conditions	Typ	Max(1)	Unit
ET	Total unadjusted error	f_{ADC} =18 MHz V_{DDA} = 1.7 to 3.6 V V_{REF} = 1.7 to 3.6 V V_{DDA} –V_{REF} < 1.2 V	±3	±4	LSB
EO	Offset error		±2	±3	
EG	Gain error		±1	±3	
ED	Differential linearity error		±1	±2	
EL	Integral linearity error		±2	±3	

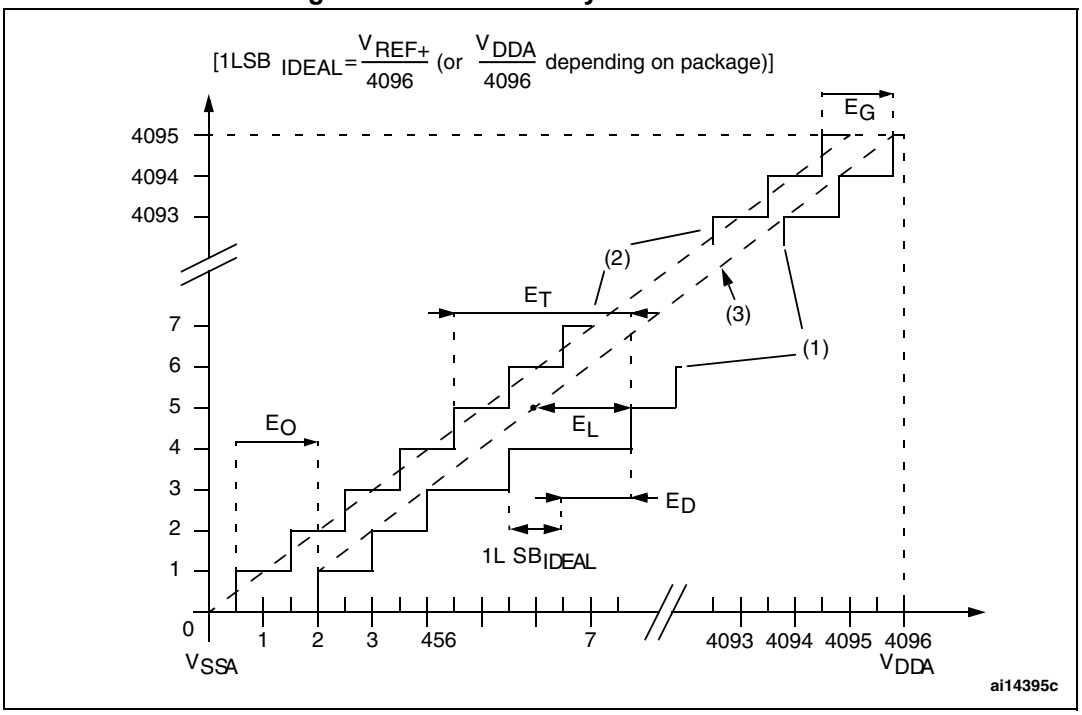
1. Guaranteed by characterization results.

Table 64. ADC static accuracy at f_{ADC} = 30 MHz

Symbol	Parameter	Test conditions	Typ	Max(1)	Unit
ET	Total unadjusted error	f_{ADC} = 30 MHz, R_{AIN} < 10 kΩ, V_{DDA} = 2.4 to 3.6 V, V_{REF} = 1.7 to 3.6 V, V_{DDA} –V_{REF} < 1.2 V	±2	±5	LSB
EO	Offset error		±1.5	±2.5	
EG	Gain error		±1.5	±4	
ED	Differential linearity error		±1	±2	
EL	Integral linearity error		±1.5	±3	

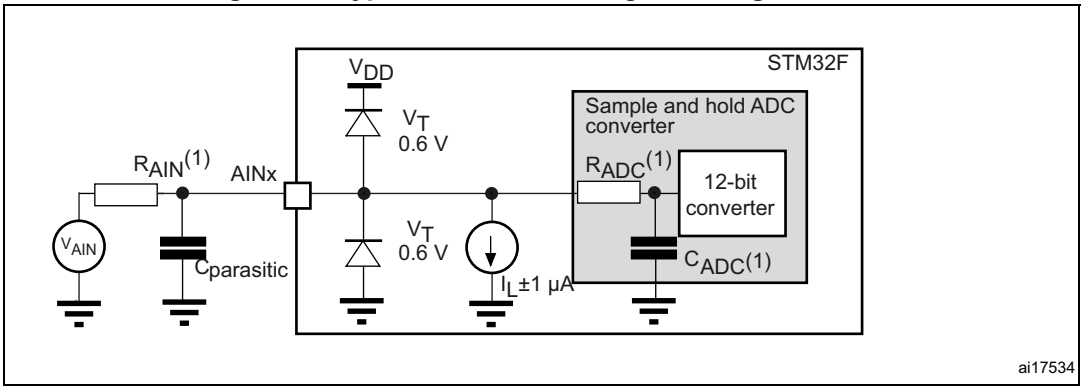
1. Guaranteed by characterization results.

Figure 41. ADC accuracy characteristics



1. See also *Table 64*.
2. Example of an actual transfer curve.
3. Ideal transfer curve.
4. End point correlation line.
5. E_T = Total Unadjusted Error: maximum deviation between the actual and the ideal transfer curves.
   EO = Offset Error: deviation between the first actual transition and the first ideal one.
   EG = Gain Error: deviation between the last ideal transition and the last actual one.
   ED = Differential Linearity Error: maximum deviation between actual steps and the ideal one.
   EL = Integral Linearity Error: maximum deviation between any actual transition and the end point correlation line.

Figure 42. Typical connection diagram using the ADC



1. Refer to *Table 62* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 5 pF). A high $C_{parasitic}$ value downgrades conversion accuracy. To remedy this, f_{ADC} should be reduced.

The 20mA output drive requirement in Fast-mode Plus is not supported. This limits the maximum load Cload supported in Fm+, which is given by these formulas:

- $Tr(SDA/SCL)=0.8473xR_pxC_{load}$
- $R_p(min)= (VDD-V_{OL}(max))/I_{OL}(max)$

Where Rp is the I2C lines pull-up. Refer to *Section 5.3.17: I/O port characteristics* for the I2C I/Os characteristics.

All I^2C SDA and SCL I/Os embed an analog filter. Refer to the table below for the analog filter characteristics:

Table 75. I2C analog filter characteristics(1)

Symbol	Parameter	Min	Max	Unit
t_{AF}	Maximum pulse width of spikes that are suppressed by the analog filter	50(2)	150(3)	ns

1. Guaranteed by characterization results.
2. Spikes with widths below $t_{AF(min)}$ are filtered.
3. Spikes with widths above $t_{AF(max)}$ are not filtered

Table 92. Asynchronous multiplexed PSRAM/NOR read timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$3T_{HCLK}-0.5$	$3T_{HCLK}+1.5$	ns
$t_{v(NOE\_NE)}$	FMC_NEx low to FMC_NOE low	$2T_{HCLK}-1$	$2T_{HCLK}+0.5$	
$t_{tw(NOE)}$	FMC_NOE low time	$T_{HCLK}-0.5$	$T_{HCLK}+0.5$	
$t_{h(NE\_NOE)}$	FMC_NOE high to FMC_NE high hold time	0	-	
$t_{v(A\_NE)}$	FMC_NEx low to FMC_A valid	-	0.5	
$t_{v(NADV\_NE)}$	FMC_NEx low to FMC_NADV low	0	0.5	
$t_{w(NADV)}$	FMC_NADV low time	$T_{HCLK}-0.5$	$T_{HCLK}+1.5$	
$t_{h(AD\_NADV)}$	FMC_AD(address) valid hold time after FMC_NADV high)	0	-	
$t_{h(A\_NOE)}$	Address hold time after FMC_NOE high	$T_{HCLK}-0.5$	-	
$t_{h(BL\_NOE)}$	FMC_BL time after FMC_NOE high	0	-	
$t_{v(BL\_NE)}$	FMC_NEx low to FMC_BL valid	-	0.5	
$t_{su(Data\_NE)}$	Data to FMC_NEx high setup time	$T_{HCLK}-2$	-	
$t_{su(Data\_NOE)}$	Data to FMC_NOE high setup time	$T_{HCLK}-2$	-	
$t_{h(Data\_NE)}$	Data hold time after FMC_NEx high	0	-	
$t_{h(Data\_NOE)}$	Data hold time after FMC_NOE high	0	-	

1. Guaranteed by characterization results.

Table 93. Asynchronous multiplexed PSRAM/NOR read-NWAIT timings(1)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FMC_NE low time	$8T_{HCLK}-1$	$8T_{HCLK}+2$	ns
$t_{w(NOE)}$	FMC_NWE low time	$5T_{HCLK}-1$	$5T_{HCLK}+1$	
$t_{su(NWAIT\_NE)}$	FMC_NWAIT valid before FMC_NEx high	$5T_{HCLK}+1.5$	-	
$t_{h(NE\_NWAIT)}$	FMC_NEx hold time after FMC_NWAIT invalid	$4T_{HCLK}+1$	-	

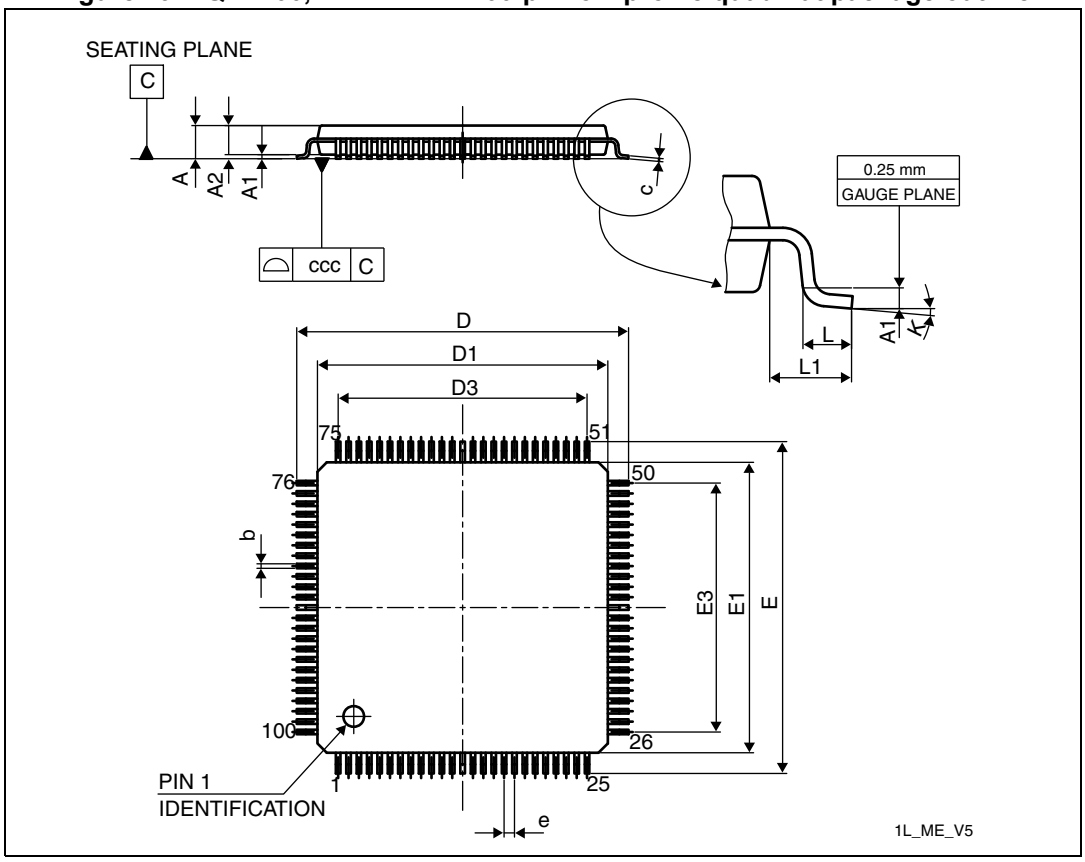
1. Guaranteed by characterization results.

6 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK® is an ST trademark.

6.1 LQFP100, 14 x 14 mm low-profile quad flat package information

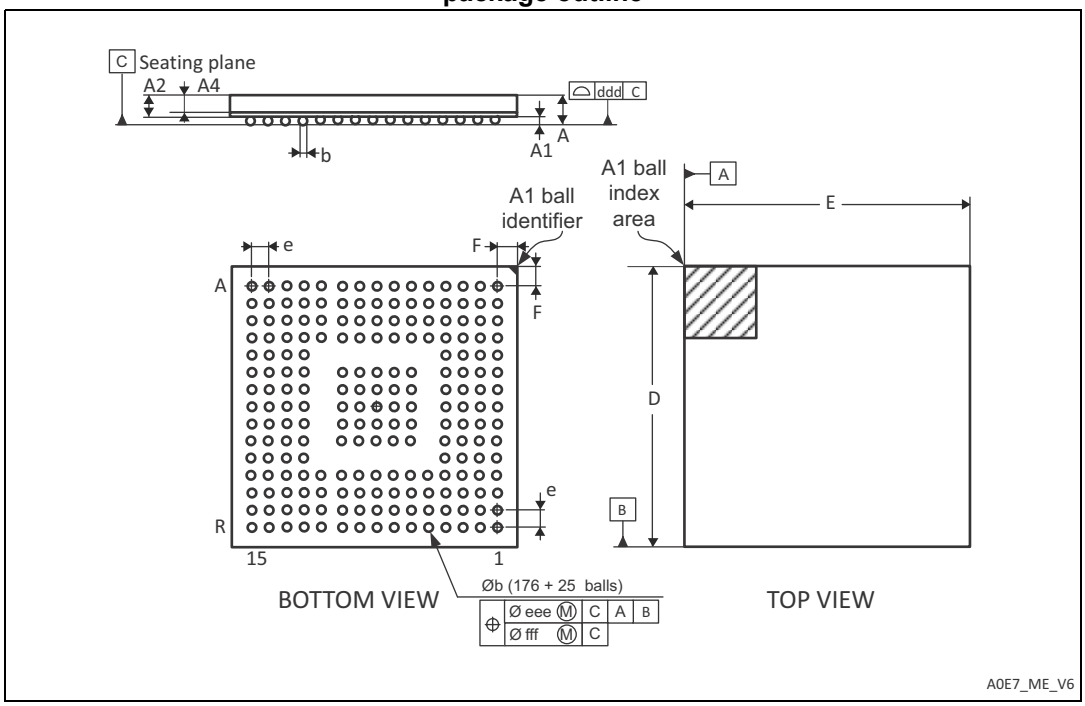
Figure 79. LQFP100, 14 x 14 mm 100-pin low-profile quad flat package outline



1. Drawing is not to scale.

6.7 UFBGA 176+25, 10 x 10 x 0.65 mm ultra thin-pitch ball grid array package information

Figure 97. UFBGA 176+25, 10 × 10 × 0.65 mm ultra thin fine-pitch ball grid array package outline



1. Drawing is not to scale.

Table 120. UFBGA 176+25, 10 × 10 × 0.65 mm ultra thin fine-pitch ball grid array package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	0.460	0.530	0.600	0.0181	0.0209	0.0236
A1	0.050	0.080	0.110	0.002	0.0031	0.0043
A2	0.400	0.450	0.500	0.0157	0.0177	0.0197
b	0.230	0.280	0.330	0.0091	0.0110	0.0130
D	9.950	10.000	10.050	0.3917	0.3937	0.3957
E	9.950	10.000	10.050	0.3917	0.3937	0.3957
e	-	0.650	-	-	0.0256	-
F	0.400	0.450	0.500	0.0157	0.0177	0.0197
ddd	-	-	0.080	-	-	0.0031
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.

6.9 Thermal characteristics

The maximum chip-junction temperature, T_J max, in degrees Celsius, may be calculated using the following equation:

T_J max = T_A max + (P_D max x Θ_{JA})

Where:

- T_A max is the maximum ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D max is the sum of P_{INT} max and $P_{I/O}$ max (P_D max = P_{INT} max + $P_{I/O}$max),
- P_{INT} max is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.

$P_{I/O}$ max represents the maximum power dissipation on output pins where:

$P_{I/O}$ max = Σ (V_{OL} × I_{OL}) + Σ((V_{DD} – V_{OH}) × I_{OH}),

taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 124. Package thermal characteristics

Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal resistance junction-ambient** LQFP100 - 14 × 14 mm / 0.5 mm pitch	43	°C/W
	Thermal resistance junction-ambient TFBGA100 - 8 × 8 mm / 0.8 mm pitch	57	
	Thermal resistance junction-ambient WLCSP143	31.2	
	Thermal resistance junction-ambient LQFP144 - 20 × 20 mm / 0.5 mm pitch	40	
	Thermal resistance junction-ambient LQFP176 - 24 × 24 mm / 0.5 mm pitch	38	
	Thermal resistance junction-ambient LQFP208 - 28 × 28 mm / 0.5 mm pitch	19	
	Thermal resistance junction-ambient UFBGA176 - 10 × 10 mm / 0.5 mm pitch	39	
	Thermal resistance junction-ambient TFBGA216 - 13 × 13 mm / 0.8 mm pitch	29	

Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.